WHAT IS CLAIMED IS:

1. A substrate for substrate comprising:

a top surface and a back surface, the surfaces being square in shape;

an end surface formed along the thickness thereof; and

a chamfered surface formed on a perimeter edge region where the end surface and the top surface meet and another region where the end surface and the back surface meet,

wherein a size of the perimeter edge of the substrate is 300 mm or more on a side and the end surface and the chamfered surface each has a roughened surface having a surface roughness (Ra) ranging from 0.03 μm to 0.3 μm.

2. A substrate for photomask as set forth in Claim 1, wherein the end surface and the chamfered surface each has a roughened surface having a surface roughness (Ra) ranging from 0.05 μm to 0.3 μm.

3. A substrate for photomask comprising:

a top surface and a back surface, the surfaces being square in shape;

an end surface formed along the thickness thereof; and

a chamfered surface formed on a perimeter edge region where the end surface and the top surface meet and another region where the end surface and the back surface meet,

wherein a size of the perimeter edge of the substrate is 300 mm or more on a side and the chamfered surface each is a roughened surface polished with an abrasive tool having a particle size ranging from #700 to #2,400.

4. A substrate for photomask comprising:

a top surface and a back surface, the surfaces being square in shape;

an end surface formed along the thickness thereof; and

a chamfered surface formed on a perimeter edge region where the end surface and the top surface meet and another region where the end surface and the back surface meet,

wherein a size of the perimeter edge of the substrate is 300 mm or more on a side and the chamfered surface is a smaller surface roughness than the end surface.

5. A substrate for photomask as set forth in Claim 4, wherein the end surface has a surface roughness (Ra) of 0.05 μm or more.

6. A photomask blank comprising:

a substrate; and

an opaque layer provided on a top surface of the substrate,

wherein the substrate including:

the top surface and a back surface, the surfaces being square in shape;

an end surface formed along the thickness thereof; and

a chamfered surface formed on a perimeter edge region where the end surface and the top surface meet and another region where the end surface and the back surface meet,

wherein a size of the perimeter edge of the substrate is 300 mm or more on a side and the end surface and the chamfered surface each has a roughened surface having a surface roughness (Ra) ranging from 0.03 μm to 0.3 μm.

7. A photomask comprising:

a substrate ; and

an opaque layer pattern provided on a top surface of the substrate,

wherein the substrate including:

the top surface and a back surface, the surfaces being square in shape;

an end surface formed along the thickness thereof; and

a chamfered surface formed on a perimeter edge region where the end surface and the top surface meet and another region where the end surface and the back surface meet,

wherein a size of the perimeter edge of the substrate is 300 mm or more on a side and the end surface and the chamfered surface each has a roughened surface having a surface roughness (Ra) ranging from 0.03 μm to 0.3 μm.

8. A substrate for photomask as set forth in Claim 1, wherein the roughened surface having a surface roughness (Ra) ranging from 0.15 μm to 0.20 μm.

9. A substrate for photomask as set forth in Claim 3, wherein the abrasive tool for polishing the chamfered surface has a particle size ranging from #800 to #1,000.

10. A substrate for photomask as set forth in Claim 3, wherein the chamfered surface is polished with the abrasive tool and an abrasive compound.

11. A photomask blank comprising:

a substrate; and

an opaque layer provided on a top surface of the substrate,

wherein the substrate including:

the top surface and a back surface, the surfaces being square in shape;

an end surface formed along the thickness thereof; and

a chamfered surface formed on a perimeter edge region where the end surface and the top surface meet and another region where the end surface and the back surface meet,

wherein a size of the perimeter edge of the substrate is 300 mm or more on a side and the chamfered surface each is a roughened surface polished with an abrasive tool having a particle size ranging from #700 to #2,400.

12. A photomask blank comprising:

a substrate; and

an opaque layer provided on a top surface of the substrate,

wherein the substrate including:

the top surface and a back surface, the surfaces being square in shape;

an end surface formed along the thickness thereof; and

a chamfered surface formed on a perimeter edge region where the end surface and the top surface meet and another region where the end surface and the back surface meet,

wherein a size of the perimeter edge of the substrate is 300 mm or more on a side and the chamfered surface is a smaller surface roughness than the end surface.

13. A photomask comprising:

a substrate; and

an opaque layer provided on a top surface of the substrate,

wherein the substrate including:

the top surface and a back surface, the surfaces being square in shape;

an end surface formed along the thickness

thereof; and

a chamfered surface formed on a perimeter edge region where the end surface and the top surface meet and another region where the end surface and the back surface meet,

wherein a size of the perimeter edge of the substrate is 300 mm or more on a side and the chamfered surface each is a roughened surface polished with an abrasive tool having a particle size ranging from #700 to #2,400.

14. A photomask comprising:

a substrate; and

an opaque layer provided on a top surface of the substrate,

wherein the substrate including:

the top surface and a back surface, the surfaces being square in shape;

an end surface formed along the thickness thereof; and

a chamfered surface formed on a perimeter edge region where the end surface and the top surface meet and another region where the end surface and the back surface meet,

wherein a size of the perimeter edge of the

substrate is 300 mm or more on a side and the chamfered surface is a smaller surface roughness than the end surface.